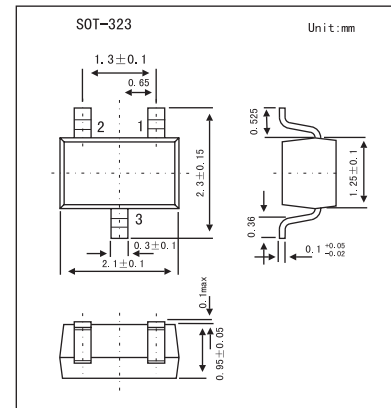


Silicon Schottky Barrier Diode

HSB276AS

■ Features

- High forward current, Low capacitance.
- HSB276AS which is interconnected in series configuration is designed for balanced mixer use.
- CMPAK package is suitable for high density surface mounting and high speed assembly.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	5	V
Reverse voltage	V_R	3	V
Average rectified current	I_o	30	mA
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 1.0 \text{ mA}$	3			V
Reverse current	I_R	$V_R = 0.5 \text{ V}$			50	μA
Forward current	I_F	$V_F = 0.5 \text{ V}$	35			mA
Capacitance	C	$V_R = 0.5 \text{ V}, f = 1 \text{ MHz}$			0.90	pF
Capacitance deviation	ΔC	$V_R = 0.5 \text{ V}, f = 1 \text{ MHz}$			0.10	pF
ESD-Capability (Note 1)		$C=200\text{pF}, R=0\ \Omega$ Both forward and reverse direction 1 pulse.	30			V

Note

1. Failure criterion ; $I_R \geq 100 \ \mu\text{A}$ at $V_R = 0.5 \text{ V}$

■ Marking

Marking	E8
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